N 10/053003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Splicant:

Leonard Forbes

Examiner:

Robert M Kunemund

Serial No.:

10/053,003

Group Art Unit:

1765

Filed:

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January 17, 2002 Docket: 1303.042US1

Title:

THREE-DIMENSIONAL COMPLETE BANDGAP PHOTONIC CRYSTAL

FORMED BY CRYSTAL MODIFICATION

RECEIVED

OCT 2 4 2003

TC 1700

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

10/23/2003 SSITHIB1 00000011 10053003 01 FC:1806

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Serial No :10/053003

Filing Date: January 17, 2002

Title: THREE-DIMENSIONAL COMPLETE BANDGAP PHOTONIC CRYSTAL FORMED BY CRYSTAL MODIFICATION

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES

-By-his-Representatives,-

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Dkt: 1303.042US1

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 1145 day of October, 2003.

Name

Signature

Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE STATEMENT BY APRLICANT (Use as many sheets as necessary) **Application Number** 10/053,003 January 17, 2002 **Filing Date** Forbes, Leonard **First Named Inventor** OCT 2 0 2003 **Group Art Unit** 1765 **Examiner Name** Kunemund, Robert THADEUNA! Attorney Docket No: 1303.042US1 Sheet 1 of 2

US PATENT DOCUMENTS							
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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
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EXAMINER DATE CONSIDERED

PTO/SB/08A(10-01)
Approved for use through 10/31/2002, OMB 651-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE
on of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** 10/053,003 STATEMENT BY APPEIGANT RECEIVED January 17, 2002 Filing Date Forbes, Leonard **First Named Inventor** OCT 2 4 2003 **Group Art Unit** 1765 **Examiner Name** Kunemund, Robert Attorney Docket No: 1303.042US1 Sheet 2 of 2

	OTHER DOCUMENTS NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²		
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